

IGBT - Field Stop, Trench

650 V, 50 A

FGH50T65UPD

Description

Using innovative field stop trench IGBT technology, ON Semiconductor's new series of field-stop trench IGBTs offer optimum performance for solar inverter, UPS, welder, and digital power generator where low conduction and switching losses are essential.

Features

- Maximum Junction Temperature: $T_J = 175^{\circ}\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.65\text{ V(Typ.) @ } I_C = 50\text{ A}$
- 100% of Parts Tested I_{LM} (Note 2)
- High Input Impedance
- Tightened Parameter Distribution
- Short Circuit Ruggedness $> 5\text{ }\mu\text{s @ } 25^{\circ}\text{C}$
- This Device is Pb-Free and is RoHS Compliant

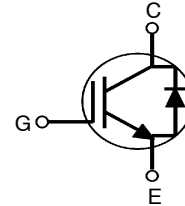
Applications

- Solar Inverter, UPS, Welder, Digital Power Generator
- Telecom, ESS



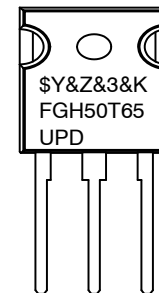
ON Semiconductor®

www.onsemi.com



TO-247-3LD
CASE 340CK

MARKING DIAGRAMS



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FGH50T65UPD	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

FGH50T65UPD

ABSOLUTE MAXIMUM RATINGS

Description		Symbol	Ratings	Unit
Collector to Emitter Voltage		V_{CES}	650	V
Gate to Emitter Voltage		V_{GES}	± 20	V
Transient Gate to Emitter Voltage			± 25	V
Collector Current	$T_C = 25^{\circ}\text{C}$	I_C	100	A
Collector Current	$T_C = 100^{\circ}\text{C}$		50	A
Pulsed Collector Current (Note 1)		I_{CM}	150	A
Clamped Inductive Load Current (Note 2)	$T_C = 25^{\circ}\text{C}$	I_{LM}	150	A
Diode Forward Current	$T_C = 25^{\circ}\text{C}$	I_F	60	A
Diode Forward Current	$T_C = 100^{\circ}\text{C}$		30	A
Pulsed Diode Maximum Forward Current (Note 1)		I_{FM}	150	A
Maximum Power Dissipation	$T_C = 25^{\circ}\text{C}$	P_D	340	W
Maximum Power Dissipation	$T_C = 100^{\circ}\text{C}$		170	W
Short Circuit Withstand Time	$T_C = 25^{\circ}\text{C}$	SCWT	5	μs
Operating Junction Temperature		T_J	-55 to $+175$	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 to $+175$	$^{\circ}\text{C}$
Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		T_L	300	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: Pulse width limited by max. junction temperature.
2. $I_C = 150\text{ A}$, $V_{ce} = 400\text{ V}$, $R_g = 10\ \Omega$

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Case (IGBT)	$R_{\theta JC}$	0.44	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Diode)	$R_{\theta JC}$	1.2	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	40	$^\circ\text{C/W}$

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH50T65UPD	FGH50T65UPD	TO-247-3LD	Tube	N/A	N/A	30

ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector to Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0\text{ V}$, $I_C = 1\text{ mA}$	650	–	–	V
Temperature Coefficient of Breakdown Voltage	$\Delta BV_{CES} / \Delta T_J$	$V_{GE} = 0\text{ V}$, $I_C = 250\ \mu\text{A}$		0.65		$\text{V}/^\circ\text{C}$
Collector Cut-Off Current	I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0\text{ V}$	–	–	250	μA
G–E Leakage Current	I_{GES}	$V_{GE} = V_{GES}$, $V_{CE} = 0\text{ V}$	–	–	± 400	nA

ON CHARACTERISTICS

G–E Threshold Voltage	$V_{GE(th)}$	$I_C = 50\text{ mA}$, $V_{CE} = V_{GE}$	4.0	6.0	7.5	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{ A}$, $V_{GE} = 15\text{ V}$	–	1.65	2.3	V
		$I_C = 50\text{ A}$, $V_{GE} = 15\text{ V}$, $T_C = 175^\circ\text{C}$	–	2.1	–	V

FGH50T65UPD

ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ies}	V _{CE} = 30 V, V _{GE} = 0 V, f = 1 MHz	–	3450	4710	pF
Output Capacitance	C _{oes}		–	110	146	pF
Reverse Transfer Capacitance	C _{res}		–	60	90	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(on)}	V _{CC} = 400 V, I _C = 50 A, R _G = 6.0 Ω, V _{GE} = 15 V, Inductive Load, T _C = 25°C	–	32	41	ns
Rise Time	t _r		–	59	77	ns
Turn-Off Delay Time	t _{d(off)}		–	160	208	ns
Fall Time	t _f		–	22	29	ns
Turn-On Switching Loss	E _{on}		–	2.7	3.5	mJ
Turn-Off Switching Loss	E _{off}		–	0.74	0.96	mJ
Total Switching Loss	E _{ts}		–	3.44	4.46	mJ
Turn-On Delay Time	t _{d(on)}	V _{CC} = 400 V, I _C = 50 A, R _G = 6.0 Ω, V _{GE} = 15 V, Inductive Load, T _C = 175°C	–	29	–	ns
Rise Time	t _r		–	72	–	ns
Turn-Off Delay Time	t _{d(off)}		–	166	–	ns
Fall Time	t _f		–	19	–	ns
Turn-On Switching Loss	E _{on}		–	3.5	–	mJ
Turn-Off Switching Loss	E _{off}		–	1.2	–	mJ
Total Switching Loss	E _{ts}		–	4.7	–	mJ
Short Circuit Withstand Time	T _{sc}	V _{GE} = 15 V, V _{CC} = 400 V, R _g = 10 Ω	5	–	–	μs
Total Gate Charge	Q _g	V _{CE} = 400 V, I _C = 50 A, V _{GE} = 15 V	–	230	345	nC
Gate to Emitter Charge	Q _{ge}		–	31	47	nC
Gate to Collector Charge	Q _{gc}		–	130	195	nC

ELECTRICAL CHARACTERISTICS OF THE DIODE ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Diode Forward Voltage	V _{FM}	I _F = 30 A	T _C = 25°C	–	2.1	2.7	V
			T _C = 175°C	–	1.78	–	
Reverse Recovery Energy	E _{rec}	I _F = 30 A, di _F /dt = 200 A/μs	T _C = 175°C	–	46	–	μJ
Diode Reverse Recovery Time	t _{rr}		T _C = 25°C	–	41	53	ns
			T _C = 175°C	–	144	–	
Diode Reverse Recovery Charge	Q _{rr}		T _C = 25°C	–	76	106	nC
		T _C = 175°C	–	486	–		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS

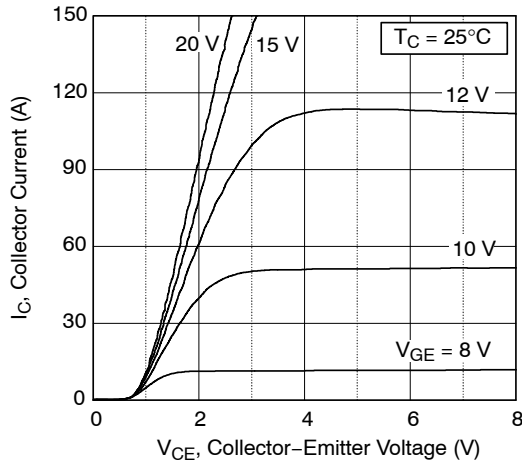


Figure 1. Typical Output Characteristics

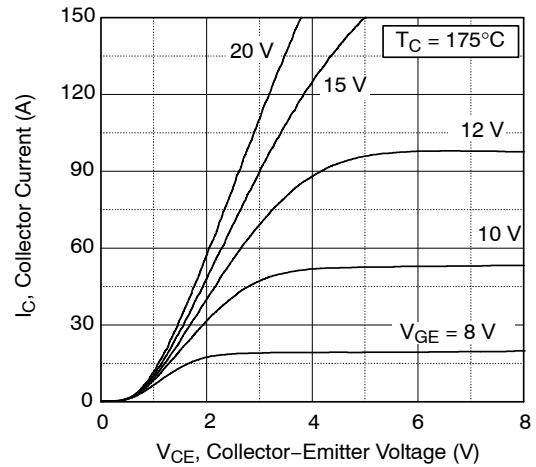


Figure 2. Typical Output Characteristics

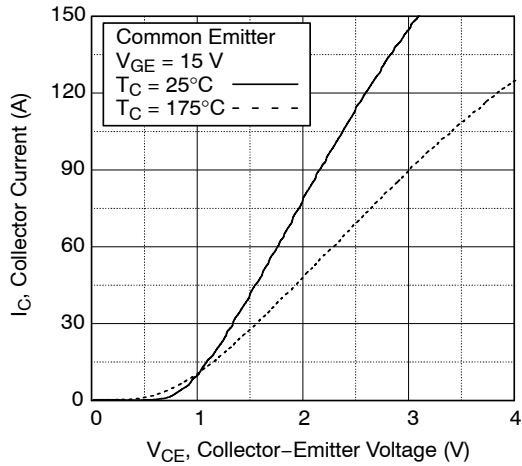


Figure 3. Typical Saturation Voltage Characteristics

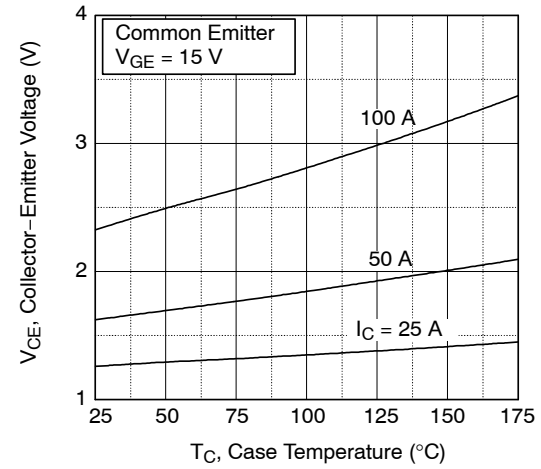


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

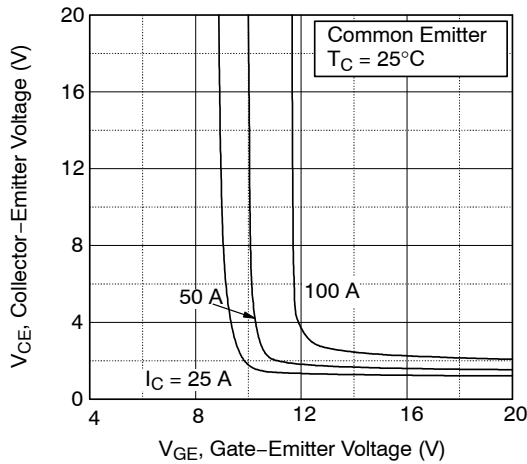


Figure 5. Saturation Voltage vs. V_{GE}

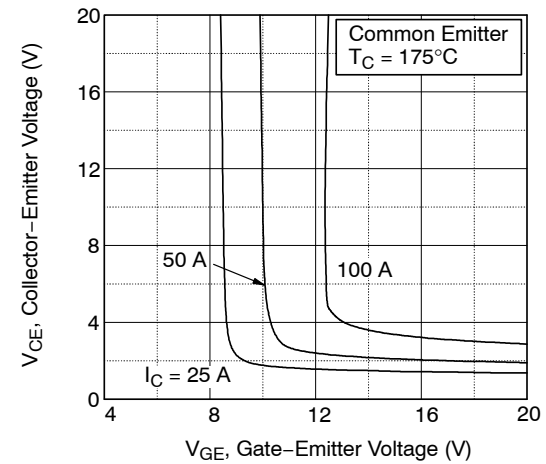


Figure 6. Saturation Voltage vs. V_{GE}

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

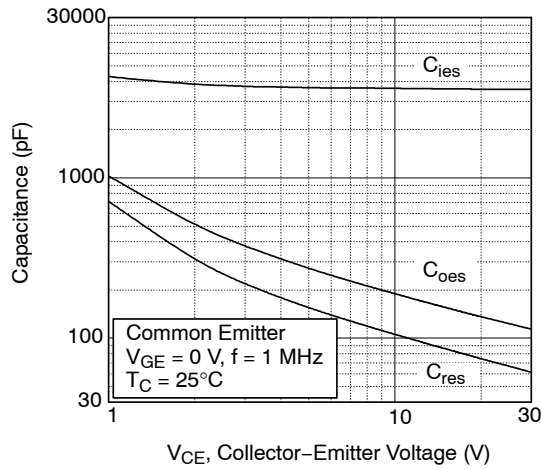


Figure 7. Capacitance Characteristics

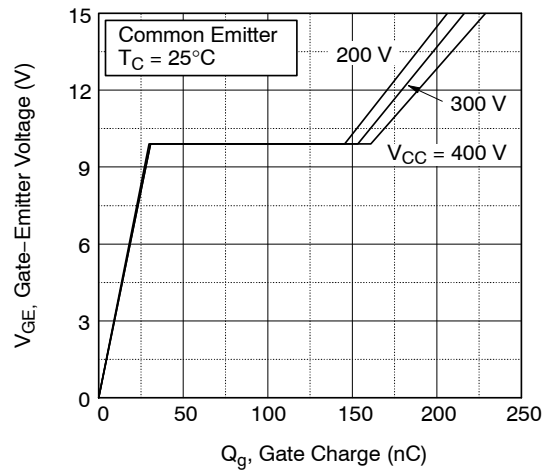


Figure 8. Gate Charge Characteristics

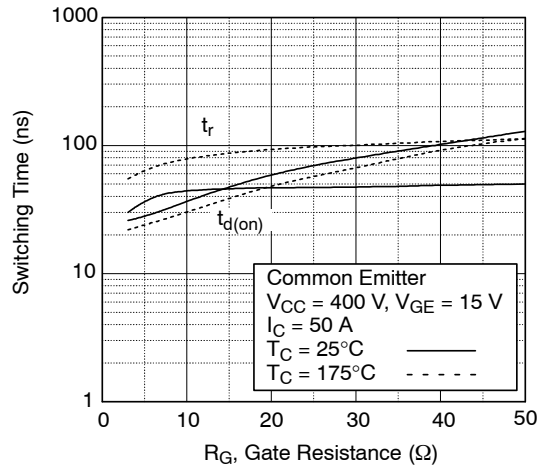


Figure 9. Turn-On Characteristics vs. Gate Resistance

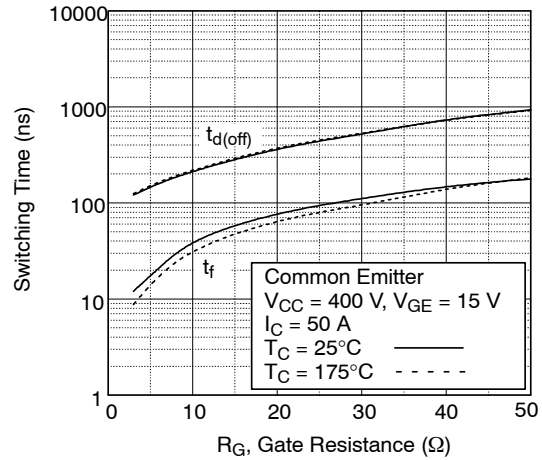


Figure 10. Turn-Off Characteristics vs. Gate Resistance

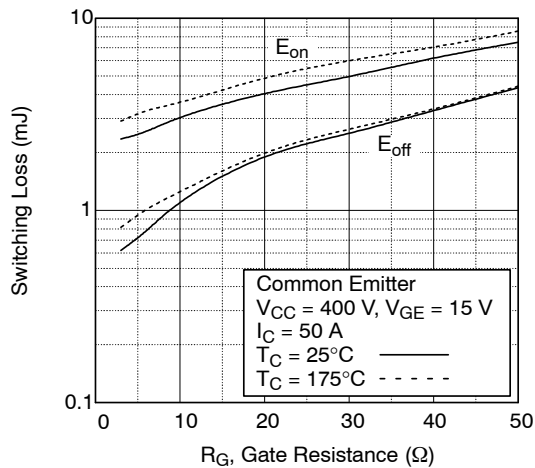


Figure 11. Switching Loss vs. Gate Resistance

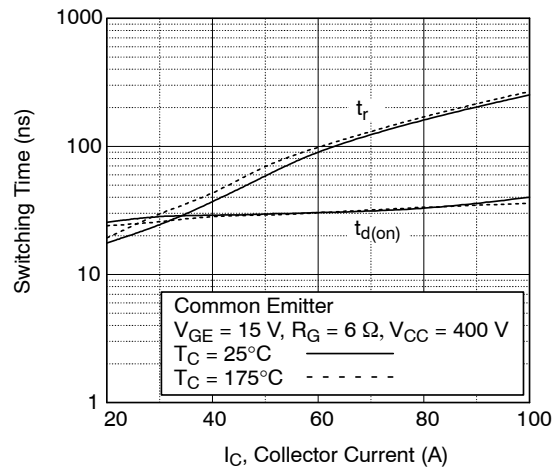


Figure 12. Turn-On Characteristics vs. Collector Current

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

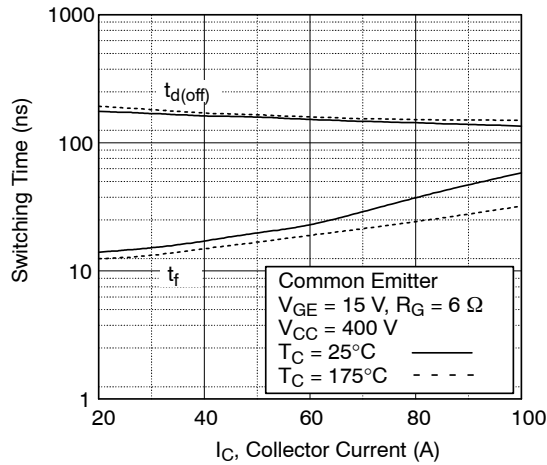


Figure 13. Turn-Off Characteristics vs. Collector Current

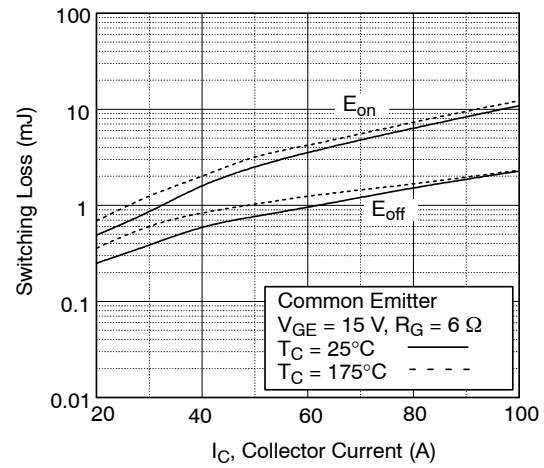


Figure 14. Switching Loss vs. Collector Current

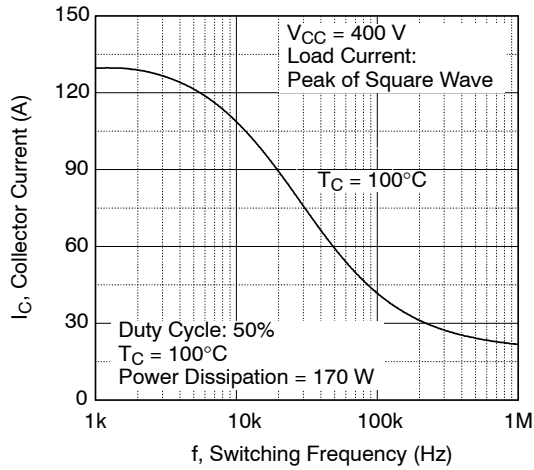


Figure 15. Load Current vs. Frequency

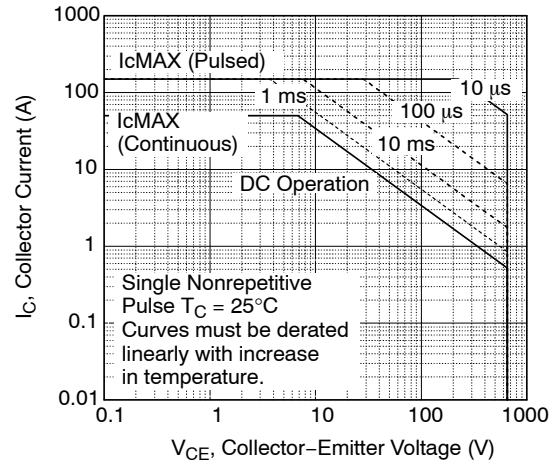


Figure 16. SOA Characteristics

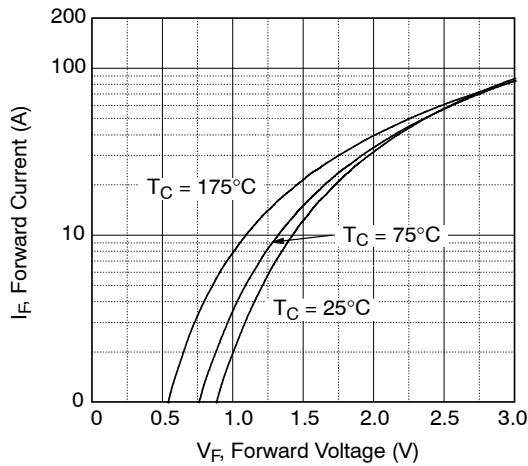


Figure 17. Forward Characteristics

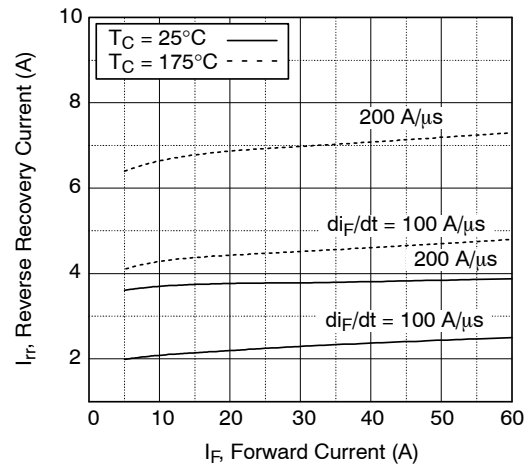


Figure 18. Reverse Recovery Current

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

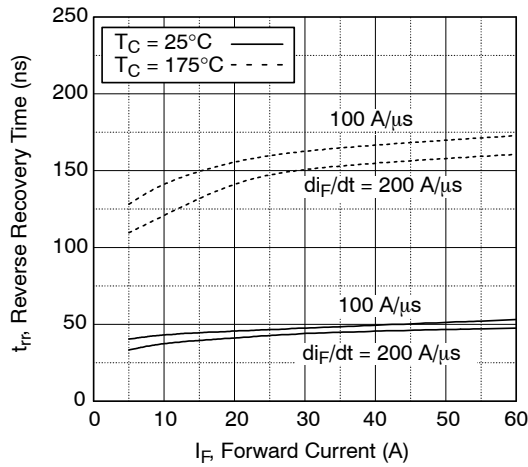


Figure 19. Reverse Recovery Time

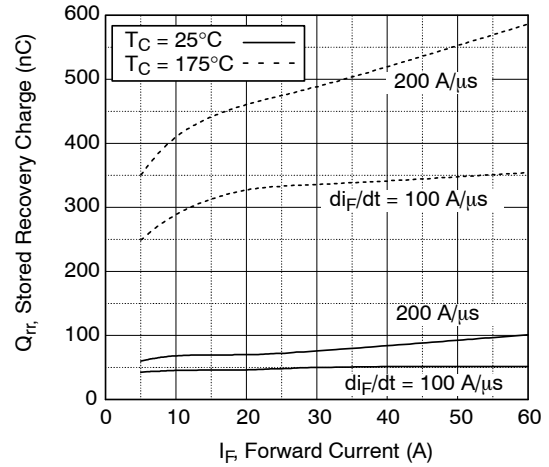


Figure 20. Stored Charge

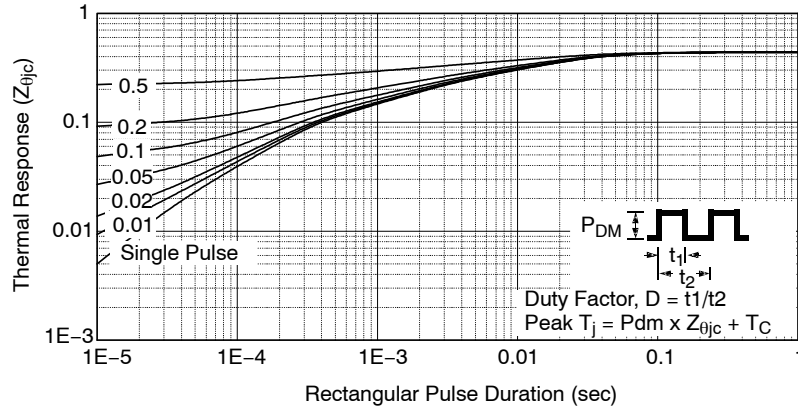


Figure 21. Transient Thermal Impedance of IGBT

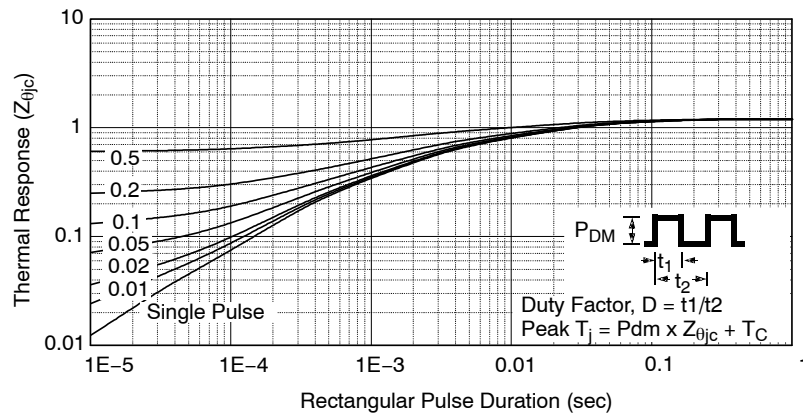


Figure 22. Transient Thermal Impedance of Diode

TO-247-3LD SHORT LEAD
CASE 340CK
ISSUE A

DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC
MARKING DIAGRAM*


XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
ϕP	3.51	3.58	3.65
$\phi P1$	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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DESCRIPTION:	TO-247-3LD SHORT LEAD	PAGE 1 OF 1

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